Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	("5412600").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/10 14:49
L2	6	(("6291853") or ("6417086") or ("5994733")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/10 14:50
L3	7	("4527259" "4797856" "4868619" "4990979" "5021999" "5051796" "5278439").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/10 14:52
L4	30	("5412600").URPN.	USPAT	OR	ON	2005/08/10 14:52
L5	186847	(ONO or (oxide near4 nitride) or O-N-O)	US-PGPUB; USPAT; EPO; JPO; DERWENT;	OR	OFF	2005/08/10 14:56
		·	IBM_TDB			
L6	18617	(float\$4 near gate) same (control\$4 near gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/10 14:56
L7	81579	(flash near memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/10 14:56
L8	3371	L5 same L6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/10 14:56
L9	2118	L8 and L7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/10 14:56
L10	1939	L9 and cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/10 14:56

L11	687	L10 and peripheral	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/10 14:56
L12	396	L11 and ((@ad<"20010626") or (@rlad<"20010626"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/10 14:56

	1			·	,	
Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	("5412600").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/10 15:08
L2	6	(("6291853") or ("6417086") or ("5994733")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/10 14:50
L3	7	("4527259" "4797856" "4868619" "4990979" "5021999" "5051796" "5278439").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/10 14:52
L4	30	("5412600").URPN.	USPAT	OR	ON	2005/08/10 14:52
L5	186847	(ONO or (oxide near4 nitride) or O-N-O)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/10 14:56
L6	18617	(float\$4 near gate) same (control\$4 near gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/10 14:56
L7	81579	(flash near memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/10 14:56
L8	3371	L5 same L6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/10 14:56
L9	2118	L8 and L7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/10 14:56
L10	1939	L9 and cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/10 14:56

L11	687	L10 and peripheral	US-PGPUB; USPAT;	OR	OFF	2005/08/10 14:56
			EPO; JPO; DERWENT; IBM_TDB			
L12	396	L11 and ((@ad<"20010626") or (@rlad<"20010626"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/10 15:11
L13	2	("4797856").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/10 15:09
L14	179	(conformal near4 nitride) and flash	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/10 15:11
L15	119	L14 and ((@ad<"20010626") or (@rlad<"20010626"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/10 15:21
L16	465	(pattern\$6 or etch\$6) near8 (second adj polysilicon) near8 insulating	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/10 15:20
L17	300	16 and cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/10 15:20
L18	116	17 and peripheral	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/10 15:21
L19	103	18 and ((@ad<"20010626") or (@rlad<"20010626"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/10 15:31
L20	4112	"select gate"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/10 15:31

L21	1293	20 same "control gate"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/10 15:31
L22	953	21 same "floating gate"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/10 15:31
L23	460	22 and "select transistor"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/10 15:32
L24	167	23 and peripheral	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/10 15:32
L25	167	24 and cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR .	OFF	2005/08/10 15:32